



**DMN6140L** 

#### 60V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
60V	$140 \text{m}\Omega$ @ $V_{GS} = 10 \text{V}$	2.3A
000	170mΩ @ $V_{GS} = 4.5V$	2.1A

## **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- DC-DC Converters
- **Power Management Functions**
- Analog Switch

## **Features and Benefits**

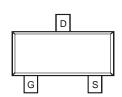
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

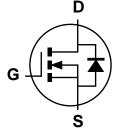
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.0072 grams (Approximate)







Pin Configuration



**Equivalent Circuit** 

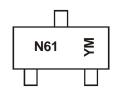
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6140L-7	SOT23	3,000/Tape & Reel
DMN6140L-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



N61 = Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011)M = Month (ex: 9 = September)

Date Code Key

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α	I	3	С		D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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## **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units		
Drain-Source Voltage		V <sub>DSS</sub>	60	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V	
		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	1.6 1.2	А	
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	2.0 1.6	А	
Steady $T_A = +25$ State $T_A = +70$			ID	2.3 1.8	А	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	2.9 2.3	А	
Maximum Continuous Body Diode Forward Current	I <sub>S</sub>	1.5	Α			
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	10	А	

# **Thermal Characteristics** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	р	0.7	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	$P_{D}$	0.4	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	183	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	115	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	Ъ	1.3	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	$P_D$	0.8	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	<u> </u>	94		
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	61	°C/W	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	39		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)			•			•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		
Static Drain-Source On-Resistance			92	140	mΩ	$V_{GS} = 10V, I_D = 1.8A$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	1	115	170	11122	$V_{GS} = 4.5V, I_D = 1.3A$		
Forward Transfer Admittance	Y <sub>fs</sub>		2.2	_	S	$V_{DS} = 15V, I_{D} = 1.8A$		
Diode Forward Voltage	$V_{SD}$	_	0.75	1.0	V	$V_{GS} = 0V, I_S = 0.45A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C <sub>iss</sub>	1	315			.,		
Output Capacitance	Coss	l	18	l	pF	$V_{DS} = 40V, V_{GS} = 0V$ f = 1.0MHz		
Reverse Transfer Capacitance	Crss		16	_		1 = 1.000112		
Gate Resistnace	$R_g$	_	0.65	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$		
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$		8.6	_		V 90V L 4 94		
Total Gate Charge (V <sub>GS</sub> = 5V)	Qg	_	4.1	_	0			
Gate-Source Charge	$Q_{gs}$	_	1.0	_	nC	$V_{DS} = 30V, I_D = 1.8A$		
Gate-Drain Charge	$Q_{gd}$	_	1.7	_				
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.6	_				
Turn-On Rise Time	t <sub>r</sub>	_	3.6	_		$V_{DS} = 30V, V_{GS} = 10V,$		
Turn-Off Delay Time	t <sub>D(off)</sub>		16.3	_	ns	$R_G = 6.0\Omega$ , $I_D = 1.8A$		
Turn-Off Fall Time	t <sub>f</sub>	_	2.7	_				
Reverse Recovery Time	t <sub>rr</sub>	_	16.8	_	ns	1 4 0 4 1/4 4 400 4/4		
Reverse Recovery Charge	Qrr		9.0	_	$\frac{1}{1} = 1.8A, di/dt = 100A/\mu s$			

Notes:

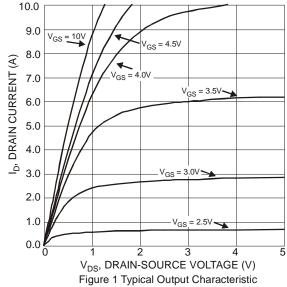
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1in. square copper plate.
- 7 .Short duration pulse test used to minimize self-heating effect.
- Guaranteed by design. Not subject to production testing.

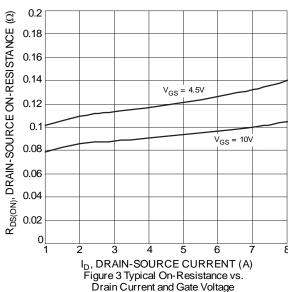
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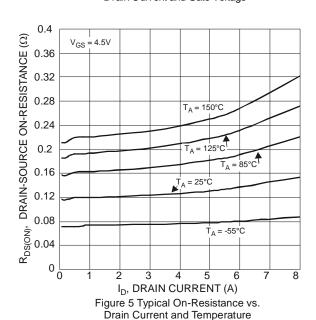
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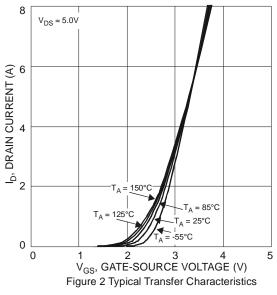
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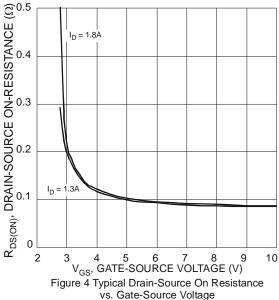


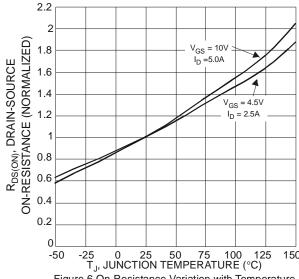








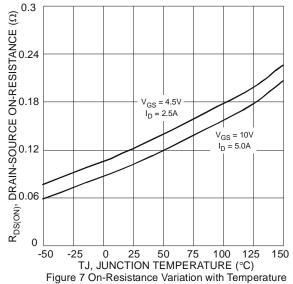


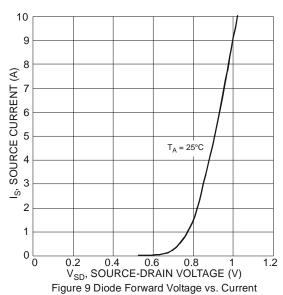


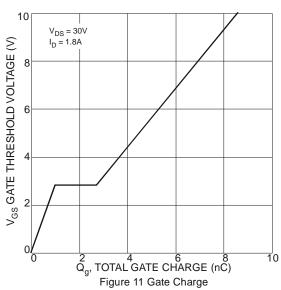
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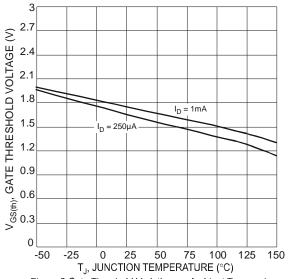
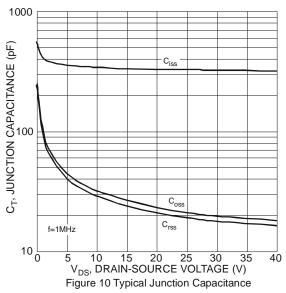
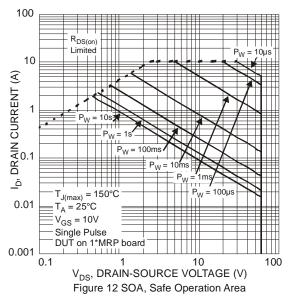
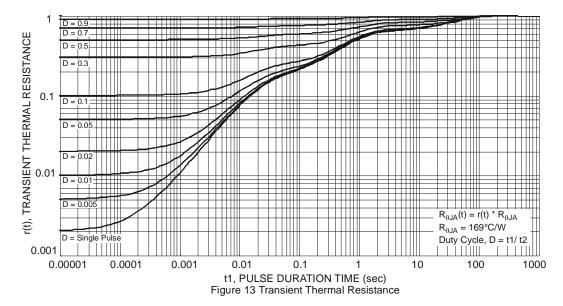


Figure 8 Gate Threshold Variation vs. Ambient Temperature



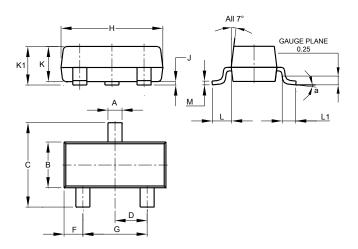






## **Package Outline Dimensions**

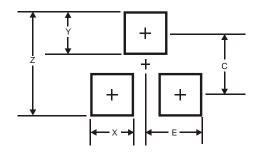
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23							
Dim	Min Max Ty						
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890 1.00 0.97						
K1	0.903	1.10	1.025				
٦	0.45 0.61 0.55						
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
α	8°						
All	All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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